

#### NCE P-Channel Enhancement Mode Power MOSFET

#### **Description**

The NCE60P04R uses advanced trench technology and design to provide excellent  $R_{\text{DS(ON)}}$  with low gate charge .This device is well suited for use as a load switch or in PWM applications.

#### **General Features**

•  $V_{DS} = -60V, I_{D} = -4.3A$ 

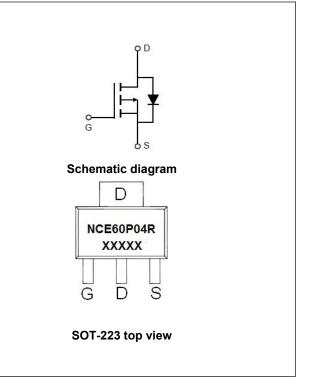
 $R_{DS(ON)}$  <120m $\Omega$  @  $V_{GS}$ =-10V

 $R_{DS(ON)}$  <170m $\Omega$  @  $V_{GS}$ =-4.5V

- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

#### **Application**

- Load switch
- PWM application



### **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE60P04R	NCE60P04R	SOT-223-3L	Ø330mm	12mm	2500 units

#### Absolute Maximum Ratings (T<sub>C</sub>=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	-60	V
Gate-Source Voltage	V <sub>G</sub> s	±20	V
Drain Current-Continuous	I <sub>D</sub>	-4.3	A
Pulsed Drain Current	I <sub>DM</sub>	-20	Α
Maximum Power Dissipation	P <sub>D</sub>	3.1	W
Operating Junction and Storage Temperature Range	$T_{J},T_{STG}$	-55 To 150	$^{\circ}$

#### **Thermal Characteristic**

Thermal Resistance, Junction-to-Ambient(Note 2)	ReJA	40.3	°C/W
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#### Electrical Characteristics (T<sub>C</sub>=25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	1					
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =-250μA	-60	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-60V,V <sub>GS</sub> =0V	-	-	-1	μΑ



## http://www.ncepower.com

# NCE60P04R

Gate-Body Leakage Current	I <sub>GSS</sub>	$V_{GS}$ =±20 $V$ , $V_{DS}$ =0 $V$	-	-	±100	nA
On Characteristics (Note 3)				•		
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS},I_{D}=-250\mu A$	-1.0		-2.5	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-4A	-	106	120	mΩ
Drain-Source On-State Resistance		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-3A	-	135	170	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =-5V,I <sub>D</sub> =-4A	-	10	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	Clss	\\ 20\\\\ 0\\	-	930	-	PF
Output Capacitance	Coss	$V_{DS}$ =-30V, $V_{GS}$ =0V,	-	85	-	PF
Reverse Transfer Capacitance	Crss	F=1.0MHz	-	35	-	PF
Switching Characteristics (Note 4)	,		•			
Turn-on Delay Time	t <sub>d(on)</sub>		-	8	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =-30V, $R_L$ =7.5 $\Omega$ ,	-	4	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =-10 $V$ , $R_{G}$ =3 $\Omega$	-	32	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	7	-	nS
Total Gate Charge	Qg	)/ 00 l /A	-	25	-	nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =-30,I <sub>D</sub> =-4A,	-	3	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =-10V	-	7	-	nC
Drain-Source Diode Characteristics			1			
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =-4A	-		-1.2	V
Diode Forward Current (Note 2)	Is		-	-	-4.3	Α
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25°C, I <sub>F</sub> =- 4A	-	25		nS
Reverse Recovery Charge	Qrr	$di/dt = -100A/\mu s^{(Note3)}$	-	31		nC

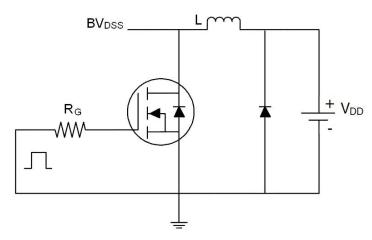
#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width  $\leq$  300 $\mu$ s, Duty Cycle  $\leq$  2%.
- 4. Guaranteed by design, not subject to production

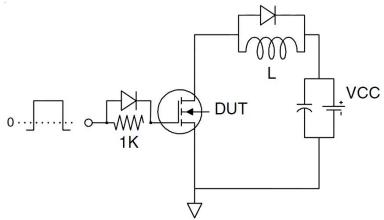


## **Test Circuit**

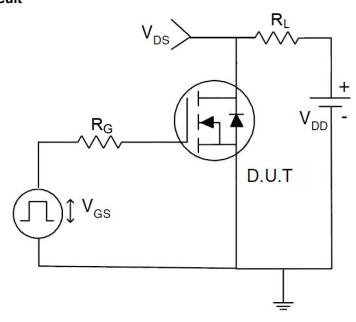
## 1) E<sub>AS</sub> test Circuit



## 2) Gate charge test Circuit



#### 3) Switch Time Test Circuit





## Typical Electrical and Thermal Characteristics (Curves)

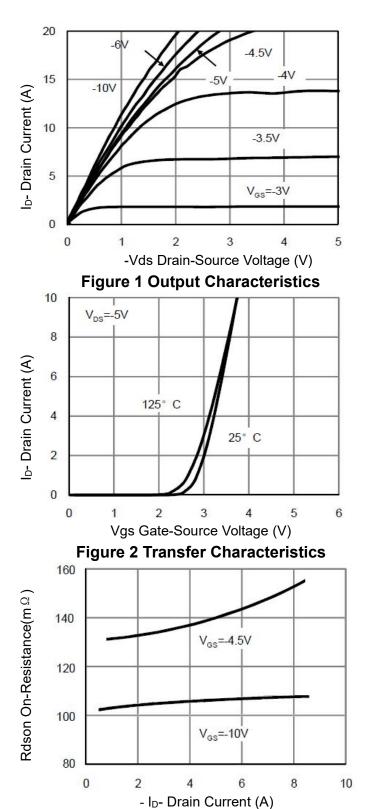
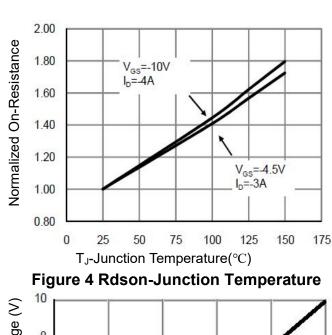
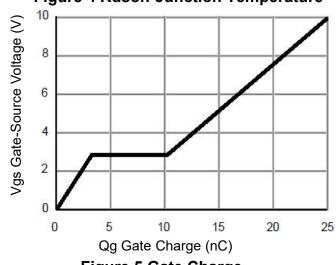


Figure 3 Rdson- Drain Current





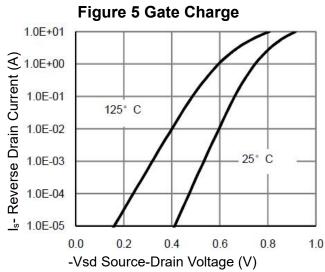
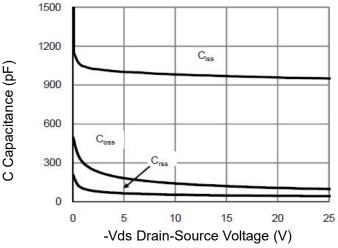


Figure 6 Source- Drain Diode Forward





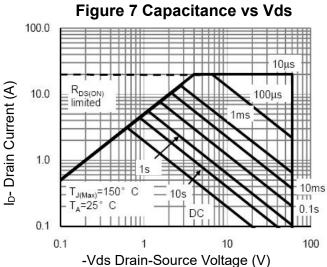


Figure 8 Safe Operation Area

BV<sub>DSS</sub> (norm) V<sub>GS</sub>=0 1.2 1.1 1.0 1.0 0.9 0.8 -50 0 50 100 T<sub>J</sub>(°C) T<sub>J</sub>-Junction Temperature(°C)

Figure 9 BV<sub>DSS</sub> vs Junction Temperature

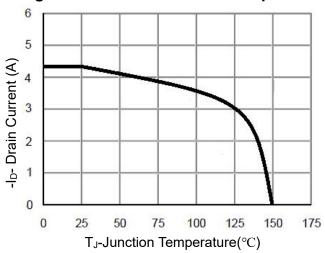


Figure 10 ID Current De-rating

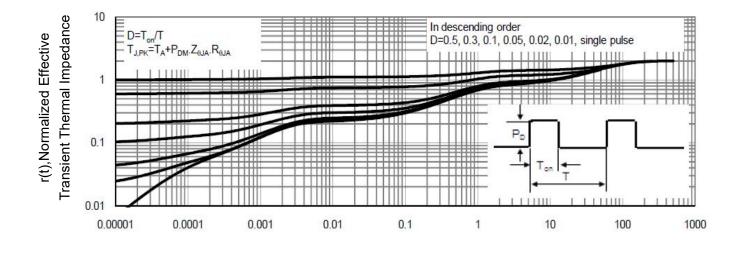
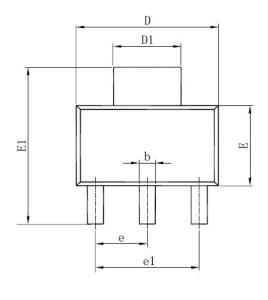


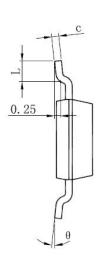
Figure 11 Normalized Maximum Transient Thermal Impedance

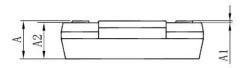
Square Wave Pluse Duration(sec)



## **SOT-223 Package Information(C)**



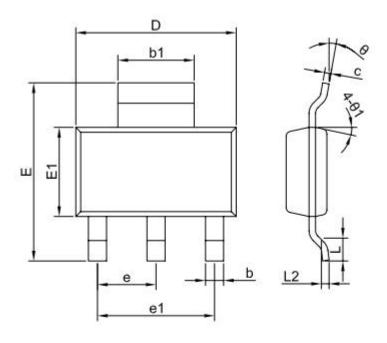


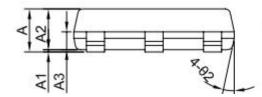


C	Dimensions In	n Millimeters	Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	1.520	1.800	0.060	0.071	
A1	0.000	0.100	0.000	0.004	
A2	1.500	1.700	0.059	0.067	
b	0.660	0.820	0.026	0.032	
С	0.250	0.350	0.010	0.014	
D	6.200	6.400	0.244	0.252	
D1	2.900	3.100	0.114	0.122	
Е	3.300	3.700	0.130	0.146	
E1	6.830	7.070	0.269	0.278	
е	2.300(BSC)		0.091(BSC)		
e1	4.500	4.700	0.177	0.185	
	0.900	1.150	0.035	0.045	
θ	0°	10°	0°	10°	



## **SOT-223 Package Information(X)**





NOTES: DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS

SYMBOL	MIN	NOM	MAX		
Α	1.55		1.80		
A1	0.02	_	0.12		
A2	1.45	1.60	1.75		
A3	0.60	0.70	0.80		
b	0.60		0.80		
b1	2.90		3.10		
С	0.24	<del></del>	0.32		
D	6.20	6.30	6.50		
E	6.70	7.00	7.30		
E1	3.30	3.50	3.70		
е	2,299REF				
e1	4.598REF				
L	0.90MIN				
L2	0.30BSC				
θ	0°	N	10°		
θ 1	10°	12°	14°		
θ 2	10°	12°	14°		

#### Notes

- 1. All dimensions are in millimeters.
- 2. Tolerance  $\pm 0.10$ mm (4 mil) unless otherwise specified
- 3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- 4. Dimension L is measured in gauge plane.
- 5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

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